Bicolor Symbol LED, 2.5x5 mm Untinted Top Diffused

Color	Туре	Technology	Angle of half intensity ±φ
High efficiency red	TLSV5100	GaAsP on GaP	50°
Green		GaP on GaP	30

Features

- Even luminance of the emitting surface
- Ideal as flush mounted panel indicators
- For DC and pulse operation
- Color mixing possible due to separate anode terminals
- Luminous intensity selected into groups
- Categorized for green color
- Wide viewing angle
- Common cathode

Applications

Indicating and illumination purposes.

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Absolute Maximum Ratings

 $T_{amb} = 25$ °C, unless otherwise specified

TLSV5100

Parameter	Test Conditions	Type	Symbol	Value	Unit
Reverse voltage per diode			V_{R}	6	V
DC forward current per diode			I_{F}	30	mA
Surge forward current per diode	$t_p \le 10 \ \mu s$		I_{FSM}	1	A
Power dissipation per diode	$T_{amb} \le 55$ °C		P_{V}	100	mW
Total power dissipation	$T_{amb} \le 55$ °C		P_{tot}	150	mW
Junction temperature			T_{j}	100	°C
Storage temperature range			T_{stg}	-55 to +100	°C
Soldering temperature	$t \le 5 \text{ s}, 2 \text{ mm}$ from body		T_{sd}	260	°C
Thermal resistance junction/ambient per diode			R_{thJA}	450	K/W
Thermal resistance junction/ambient total			R_{thJA}	300	K/W

Optical and Electrical Characteristics

 $T_{amb} = 25$ °C, unless otherwise specified

High efficiency red (TLSV5100)

Parameter	Test Conditions	Type	Symbol	Min	Тур	Max	Unit
Per diode							
Luminous intensity	$I_F = 10 \text{ mA}, I_{Vmin}/I_{Vmax} \ge 0.5$		I_V	0.63	1		mcd
Dominant wavelength	$I_F = 10 \text{ mA}$		λ_{d}	612		625	nm
Peak wavelength	$I_F = 10 \text{ mA}$		λ_{p}		635		nm
Angle of half intensity	$I_F = 10 \text{ mA}$		φ		±50		deg
Forward voltage	$I_F = 20 \text{ mA}$		$V_{\rm F}$		2	3	V
Reverse voltage	$I_R = 10 \text{ mA}$		V_R	6	15		V
Junction capacitance	$V_R = 0$, $f = 1$ MHz		C _j		50		pF

$Green\ (TLSV5100\)$

Parameter	Test Conditions	Type	Symbol	Min	Тур	Max	Unit
Per diode							
Luminous intensity	$I_F = 10 \text{ mA}, I_{Vmin}/I_{Vmax} \ge 0.5$		I_V	0.63	1		mcd
Dominant wavelength	$I_F = 10 \text{ mA}$		$\lambda_{ m d}$	562		575	nm
Peak wavelength	$I_F = 10 \text{ mA}$		λ_{p}		565		nm
Angle of half intensity	$I_F = 10 \text{ mA}$		φ		±50		deg
Forward voltage	$I_F = 20 \text{ mA}$		V_{F}		2.4	3	V
Reverse voltage	$I_R = 10 \mu A$		V_{R}	6	15		V
Junction capacitance	$V_R = 0$, $f = 1$ MHz		Cj		50		pF

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Typical Characteristics ($T_{amb} = 25$ °C, unless otherwise specified)

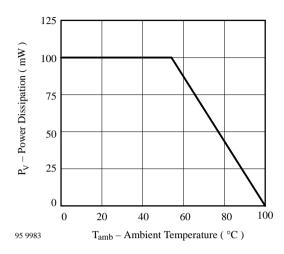


Figure 1. Power Dissipation vs. Ambient Temperature

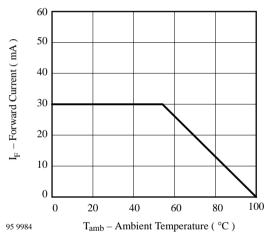


Figure 2. Forward Current vs. Ambient Temperature

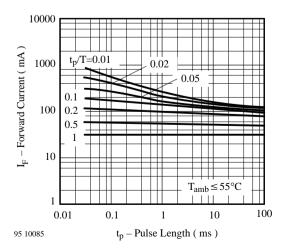


Figure 3. Forward Current vs. Pulse Length

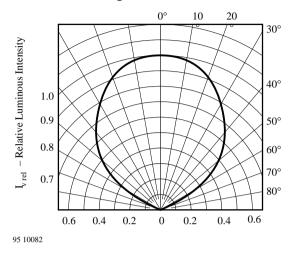


Figure 4. Rel. Luminous Intensity vs. Angular Displacement

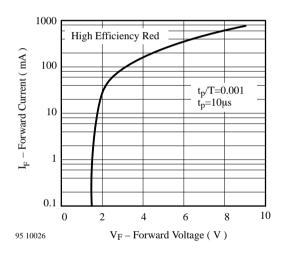


Figure 5. Forward Current vs. Forward Voltage

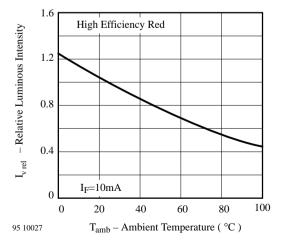


Figure 6. Rel. Luminous Intensity vs. Ambient Temperature

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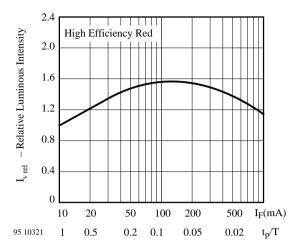


Figure 7. Rel. Lumin. Intensity vs. Forw. Current/Duty Cycle

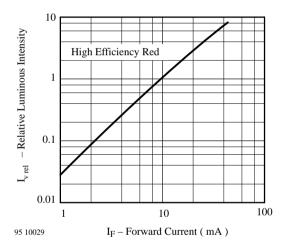


Figure 8. Relative Luminous Intensity vs. Forward Current

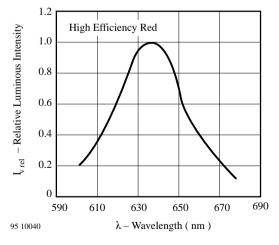


Figure 9. Relative Luminous Intensity vs. Wavelength

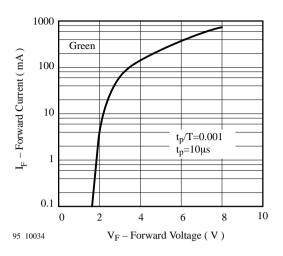


Figure 10. Forward Current vs. Forward Voltage

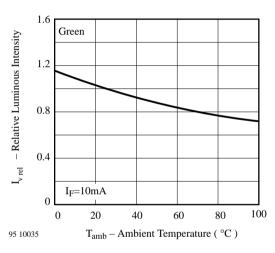


Figure 11. Rel. Luminous Intensity vs. Ambient Temperature

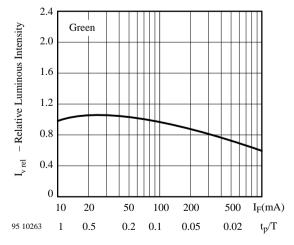
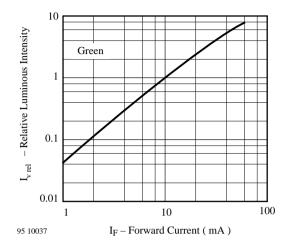


Figure 12. Rel. Lumin. Intensity vs. Forw. Current/Duty Cycle

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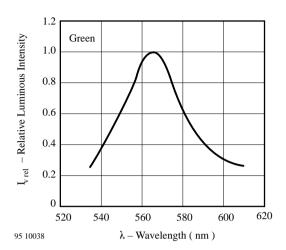


Figure 14. Relative Luminous Intensity vs. Wavelength

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TLSV5100

TELEFUNKEN Semiconductors

Ozone Depleting Substances Policy Statement

It is the policy of TEMIC TELEFUNKEN microelectronic GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

TEMIC TELEFUNKEN microelectronic GmbH semiconductor division has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

TEMIC can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use TEMIC products for any unintended or unauthorized application, the buyer shall indemnify TEMIC against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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